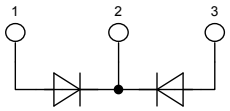
HiPerFRED²

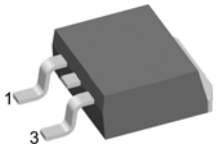
High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Common Cathode

V_{RRM} = 300 V
I_{FAV} = 2x 15 A
t_{rr} = 35 ns

Part number

DPG 30 C 300 PC





Backside: cathode

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

- Housing: TO-263 (D2Pak)
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

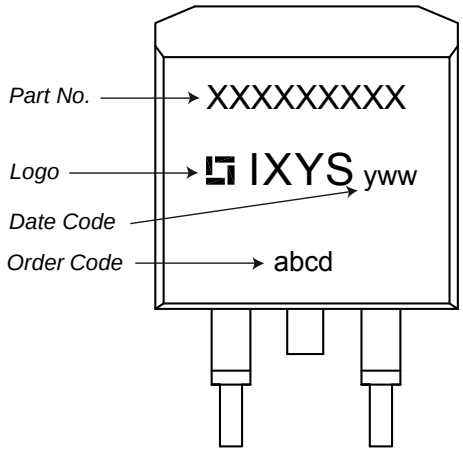
Ratings

Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RRM}	*max. repetitive reverse voltage*		T_{VJ} = 25°C			300	V
I_R	*reverse current*	V_R = 300 V	T_{VJ} = 25°C			1	µA
		V_R = 300 V	T_{VJ} = 150°C			0.08	mA
V_F	*forward voltage*	I_F = 15 A	T_{VJ} = 25°C			1.26	V
		I_F = 30 A				1.51	V
		I_F = 15 A	T_{VJ} = 150°C			1.01	V
		I_F = 30 A				1.29	V
I_{FAV}	*average forward current*	rectangular d = 0.5	T_C = 140°C			15	A
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 175°C			0.69	V
r_F	*slope resistance* }					18	mΩ
R_{thJC}	*thermal resistance junction to case*					1.70	K/W
T_{VJ}	*virtual junction temperature*			-55		175	°C
P_{tot}	*total power dissipation*		T_C = 25°C			90	W
I_{FSM}	*max. forward surge current*	t = 10 ms (50 Hz), sine	T_{VJ} = 45°C			240	A
I_{RM}	*max. reverse recovery current*		T_{VJ} = 25°C		3		A
		I_F = 15 A; V_R = 200 V	T_{VJ} = 125°C		6.5		A
t_{rr}	*reverse recovery time*	$-di_F/dt$ = 200 A/µs	T_{VJ} = 25°C		35		ns
			T_{VJ} = 125°C		55		ns
C_J	*junction capacitance*	V_R = 150 V; f = 1 MHz	T_{VJ} = 25°C		20		pF

Symbol	Definition	Conditions	Ratings min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per pin [1]			35	A
R_{thCH}	*thermal resistance case to heatsink*			0.25		K/W
T_{stg}	*storage temperature*		-55		150	°C
Weight				2		g
F_C	*mounting force with clip*		20		60	N

[1] I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.
In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Product Marking



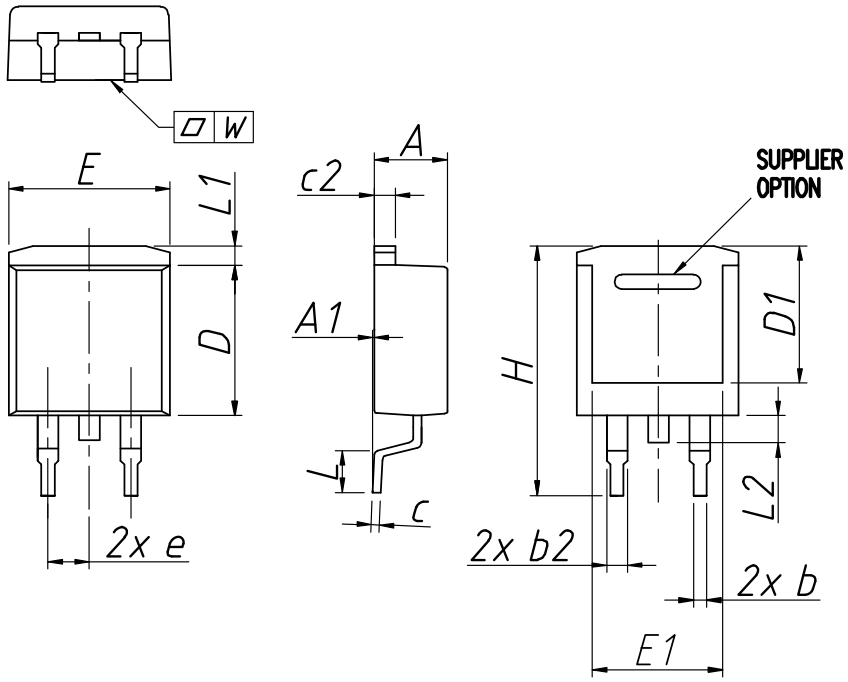
Part number

D = Diode
P = HiPerFRED
G = extreme fast
30 = Current Rating [A]
C = Common Cathode
300 = Reverse Voltage [V]
PC = TO-263AB (D2Pak) (2)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DPG 30 C 300 PC	DPG30C300PC	Tape & Reel	800	501901

Similar Part	Package	Voltage Class
DPG30C300PB	TO-220AB (3)	300
DPG30C300HB	TO-247AD (3)	300

Outlines TO-263 (D2Pak)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.029
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
E	9.65	10.41	0.380	0.410
E1	6.22	8.20	0.245	0.323
e	2,54 BSC		0,100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
L2	1.02	1.52	0.040	0.060
W	typ. 0.02	0.040	typ. 0.0008	0.0016

All dimensions conform with and/or are within JEDEC standard.

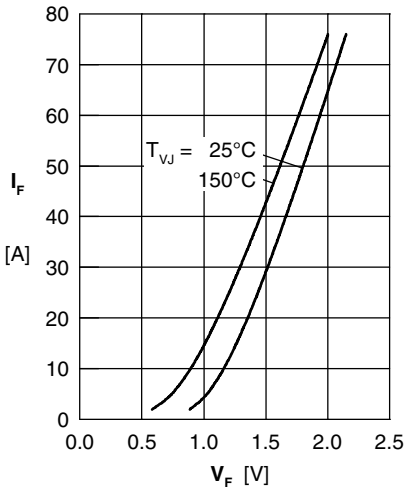


Fig. 1 Forward current I_F vs. V_F

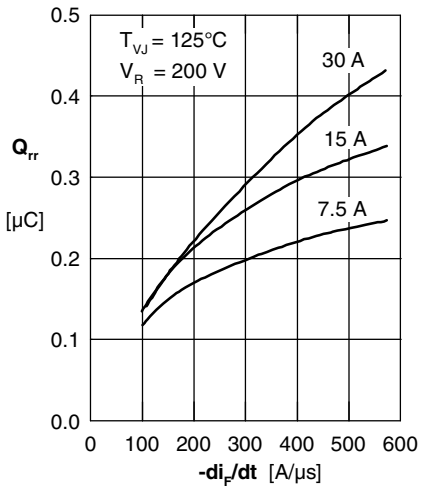


Fig. 2 Typ. reverse recovery charge Q_{rr} versus -di$_F$/dt

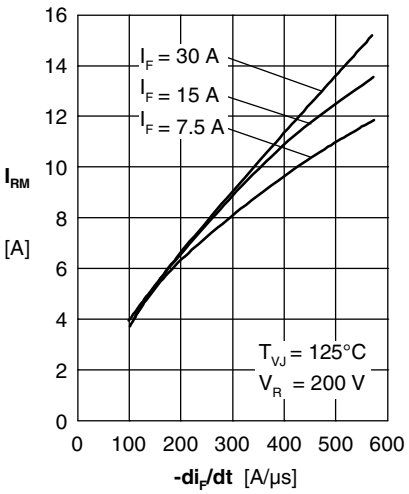


Fig. 3 Typ. peak reverse current I_{RM} versus -di$_F$/dt

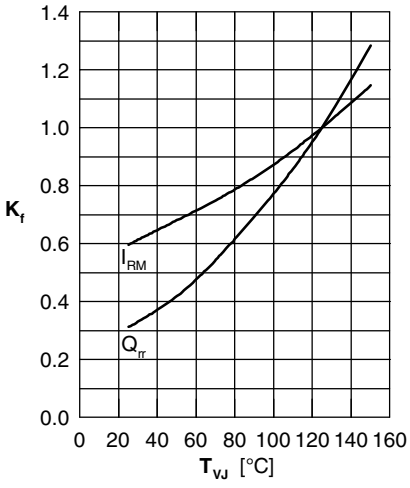


Fig. 4 Dynamic parameters Q_{rr}, I_{RM} versus T_{VJ}

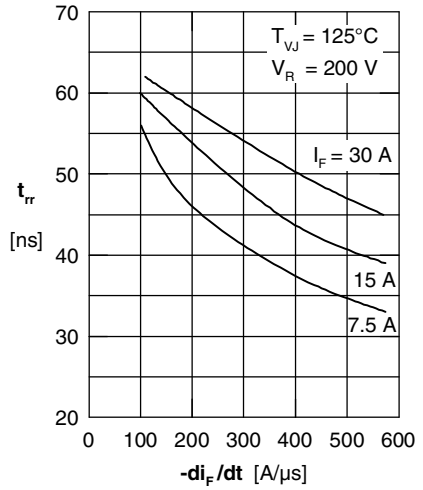


Fig. 5 Typ. recovery time t_{rr} vs. -di$_F$/dt

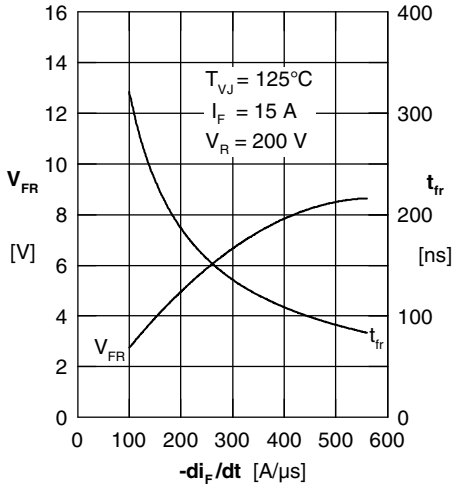


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di$_F$/dt

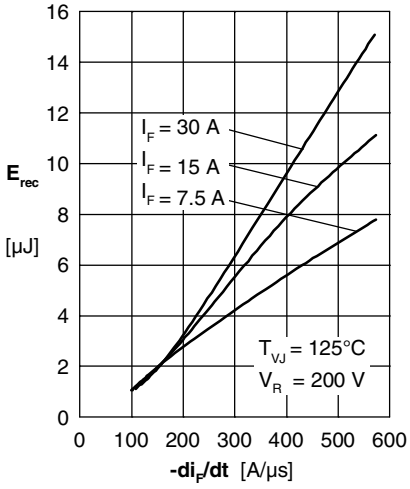


Fig. 7 Typ. recovery energy E_{rec} versus -di$_F$/dt

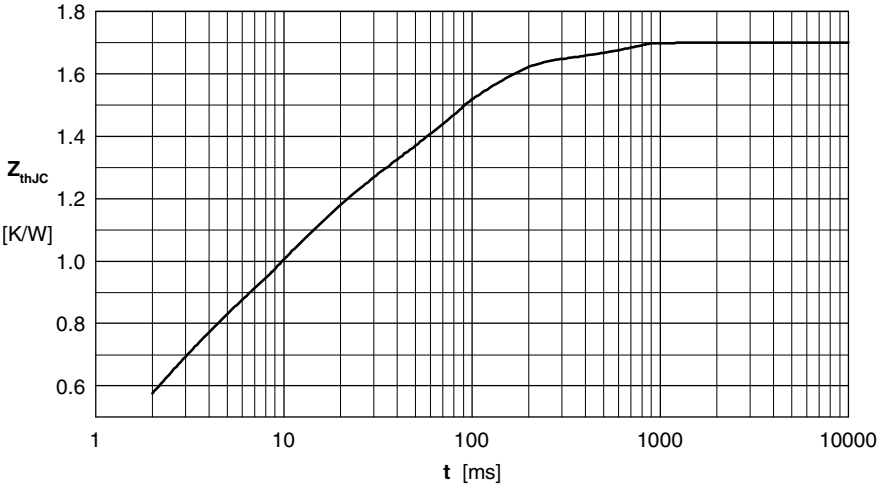


Fig. 8 Transient thermal resistance junction to case